

## PMV32UP

# 20 V, 4 A P-channel Trench MOSFET Rev. 1 — 11 March 2011

Product data sheet

#### **Product profile** 1.

#### 1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 1.2 Features and benefits

- 1.8 V drain-source on-state resistance rated
- Very fast switching
- Trench MOSFET technology

### 1.3 Applications

- Relay driver
- High-speed line driver

- High-side loadswitch
- Switching circuits

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	$T_j = 25  ^{\circ}C$		-	-	-20	V
$V_{GS}$	gate-source voltage			-8	-	8	V
$I_D$	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	-	-	-4	Α
Static char	acteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -4.5 V; $I_{D}$ = -2.4 A; $T_{j}$ = 25 °C		-	32	36	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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## 2. Pinning information

#### Table 2. Pinning information

	•	•		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		5
2	S	source	<u>    3</u>	D
3	D	drain	1 2	G S
			SOT23 (TO-236AB)	017aaa094

## 3. Ordering information

#### Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMV32UP	TO-236AB	plastic surface-mounted package; 3 leads	SOT23		

## 4. Marking

#### Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
PMV32UP	NF%

[1] % = placeholder for manufacturing site code

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## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
$V_{GS}$	gate-source voltage			-8	8	V
$I_D$	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}$	<u>[1]</u>	-	-4	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	<u>[1]</u>	-	-2.5	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-16	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	510	mW
			[1]	-	930	mW
		T <sub>sp</sub> = 25 °C		-	4150	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drai	in diode					
Is	source current	T <sub>amb</sub> = 25 °C	<u>[1]</u>	-	-1	Α

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

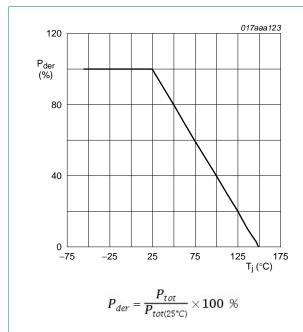


Fig 1. Normalized total power dissipation as a function of junction temperature

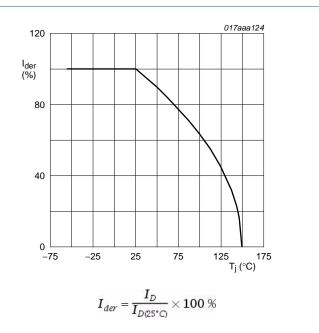
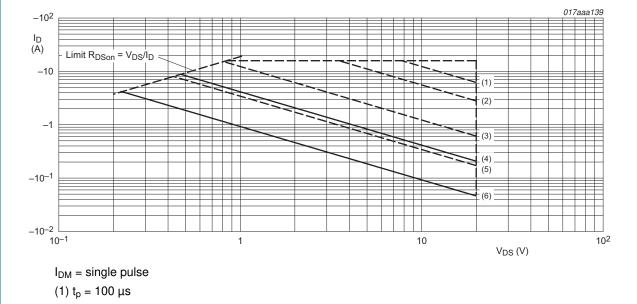


Fig 2. Normalized continuous drain current as a function of junction temperature

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- (2)  $t_p = 1 \text{ ms}$
- (3)  $t_p = 10 \text{ ms}$
- (4) DC;  $T_{sp} = 25$  °C
- $(5) t_p = 100 \text{ ms}$
- (6) DC; T<sub>amb</sub> = 25 °C; drain mounting pad 6 cm<sup>2</sup>

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

#### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance	in free air [1]	<u>[1]</u>	-	207	245	K/W
	from junction to ambient		[2]	-	117	135	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	25	30	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

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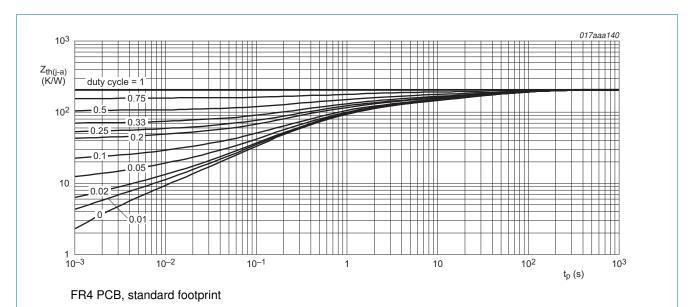


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

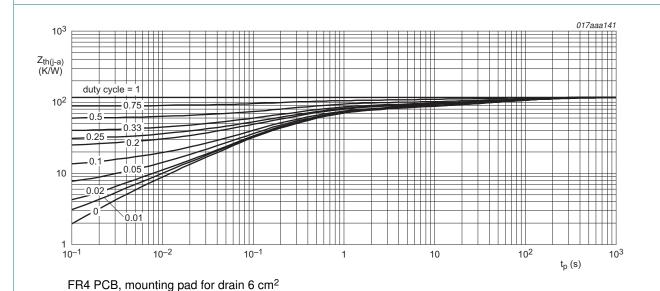


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## **Characteristics**

Table 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-0.45	-0.7	-0.95	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-10	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-100	nΑ
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -2.4 \text{ A}; T_j = 25 \text{ °C}$	-	32	36	mΩ
	resistance	$V_{GS} = -4.5 \text{ V}; I_D = -2.4 \text{ A}; T_j = 150 \text{ °C}$	-	46	53	mΩ
		$V_{GS} = -2.5 \text{ V}; I_D = -2.0 \text{ A}; T_j = 25 \text{ °C}$	-	40	46	mΩ
		$V_{GS} = -1.8 \text{ V}; I_D = -1.8 \text{ A}; T_j = 25 \text{ °C}$	-	55	73	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS} = -5 \text{ V}; I_D = -2.4 \text{ A}; T_j = 25 \text{ °C}$	-	13	-	S
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = -1 A$ ; $V_{DS} = -10 V$ ; $V_{GS} = -4.5 V$ ;	-	15.5	-	nC
$Q_{GS}$	gate-source charge	$T_j = 25  ^{\circ}C$	-	2.7	-	nC
$Q_{GD}$	gate-drain charge		-	2.2	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = -10 \text{ V}; f = 1 \text{ MHz};$	-	1890	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	175	-	pF
$C_{rss}$	reverse transfer capacitance		-	112	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = -10 \ V; \ V_{GS} = -5 \ V; \ R_{G(ext)} = 6 \ \Omega; \label{eq:VDS}$	-	13	-	ns
t <sub>r</sub>	rise time	$T_j = 25  ^{\circ}\text{C};  I_D = -1  \text{A}$	-	21	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	95	-	ns
t <sub>f</sub>	fall time		-	33	-	ns
Source-d	rain diode					
V <sub>SD</sub>	source-drain voltage	$I_S = -2.4 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$	-	-0.75	-1	V

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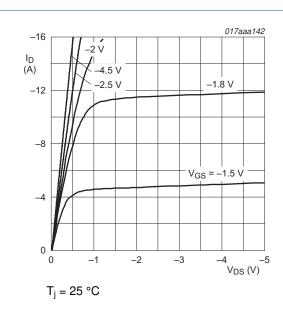
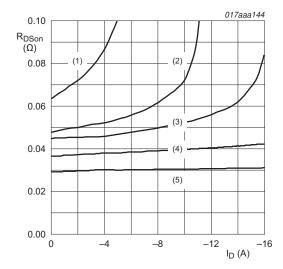


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_i = 25 \, ^{\circ}C$ 

(1)  $V_{GS} = -1.5 \text{ V}$ 

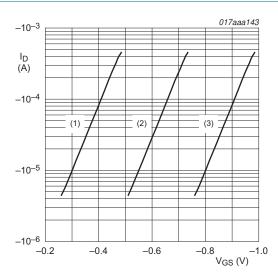
(2)  $V_{GS} = -1.8 \text{ V}$ 

(3)  $V_{GS} = -2.0 \text{ V}$ 

(4)  $V_{GS} = -2.5 \text{ V}$ 

(5)  $V_{GS} = -4.5 \text{ V}$ 

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



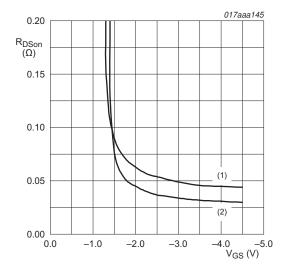
 $T_i = 25 \, ^{\circ}C; \, V_{DS} = -3 \, V$ 

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



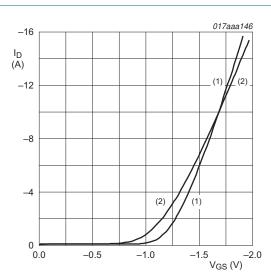
 $I_D = -2.4 A$ 

(1)  $T_i = 150 \, ^{\circ}C$ 

(2)  $T_i = 25 \, ^{\circ}C$ 

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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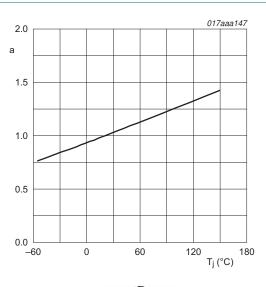


 $V_{DS} > I_{D} \times R_{DSon}$ 

(1) 
$$T_i = 25 \, ^{\circ}C$$

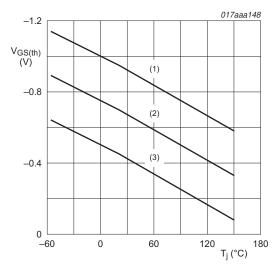
(2)  $T_i = 150 \, ^{\circ}\text{C}$ 

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$ 

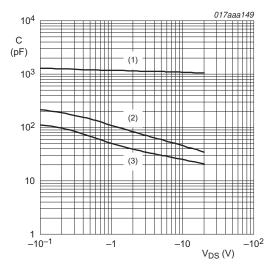
Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 $I_D$  = -0.25 mA;  $V_{DS}$  =  $V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3) C<sub>rss</sub>

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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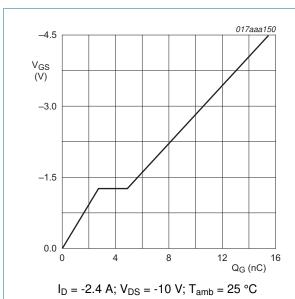
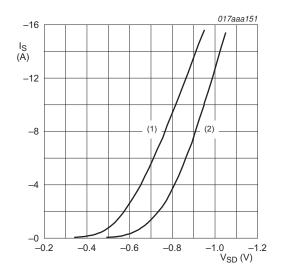


Fig 14. Gate-source voltage as a function of gate charge; typical values

Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$ 

(1)  $T_j = 150 \, ^{\circ}C$ 

(2)  $T_j = 25 \, ^{\circ}C$ 

Fig 16. Source current as a function of source-drain voltage; typical values

#### 20 V, 4 A P-channel Trench MOSFET

## 8. Package outline

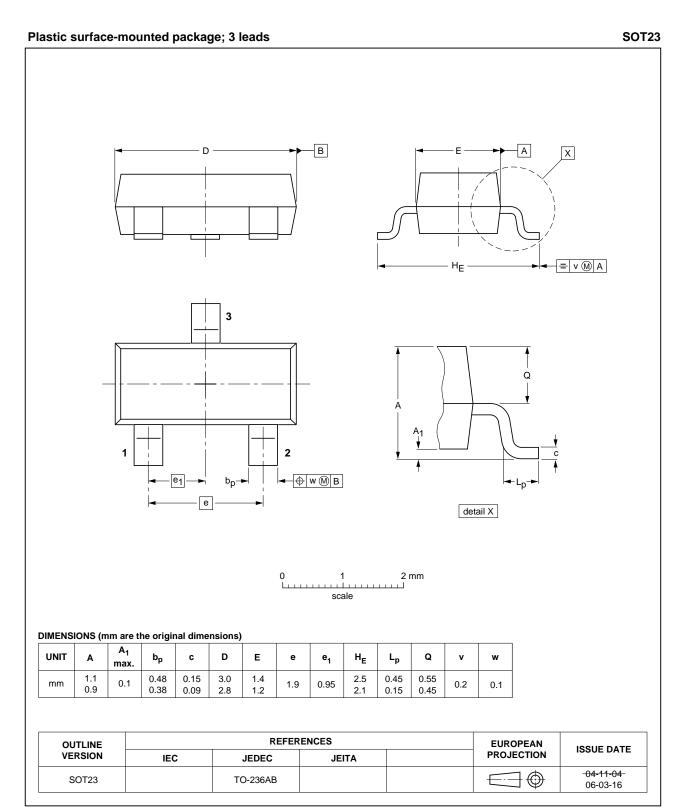


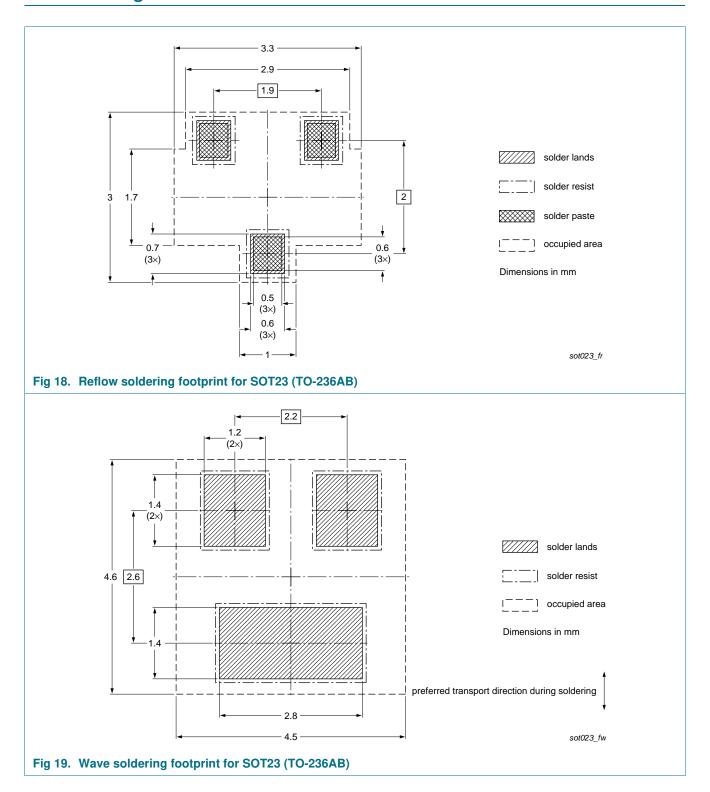
Fig 17. Package outline SOT23 (TO-236AB)

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#### 20 V, 4 A P-channel Trench MOSFET

## 9. Soldering



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## 10. Revision history

#### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMV32UP v.1	20110311	Product data sheet	-	-

#### 20 V, 4 A P-channel Trench MOSFET

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Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions'
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